SPECIFICATION AMENDMENTS

Replace the paragraph beginning at page 1, line 6 with:

The present invention relates to a method for manufacturing a semiconductor device including forming insulating gate films ~~insulating formed~~ on a substrate.

Replace the paragraph beginning at page 1, line 11 with:

In a semiconductor device, a gate insulating film is generally formed between a gate electrode and an Si substrate to prevent ~~tunnel leak~~ tunneling current leakage. The gate insulating film is generally formed of SiO_2.

Replace the paragraph beginning at page 1, line 27 with:

Therefore, on and after this generation, since the tunnel leak current will exceed the tolerable value, the SiO_2 film will not be able to be used as the gate insulating film. To cope with this problem, since the capacitance of an insulator is proportional to the dielectric constant, the ~~tunnel leak~~ tunneling leakage current can be suppressed if a metal oxide film (high-k material) is used as the gate insulating film to thicken the physical thickness of the gate insulating film.

Replace the paragraph beginning at page 3, line 21 with:

Fig. 4 shows the results of experiments conducted for examining the relationship between supply voltages and ~~leak~~ leakage currents for a manufactured semiconductor device